Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low $V_F = 0.42 \text{ V}$ at $I_F = 5 \text{ A}$

Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- Pb-Free and Halide-Free Packages are Available

Typical Applications

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

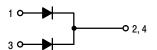


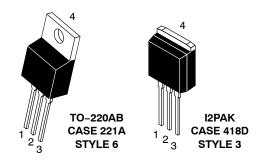
ON Semiconductor®

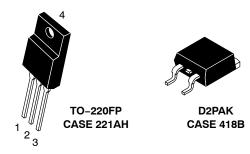
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VERY LOW FORWARD VOLT-AGE, LOW LEAKAGE SCHOT-TKY BARRIER RECTIFIERS 30 AMPERES, 100 VOLTS

PIN CONNECTIONS







ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V _{RRM} V _{RWM} V _R	100	V
Average Rectified Forward Current (Rated V_R , $T_C = 125$ °C)	Per device Per diode	I _{F(AV)}	30 15	А
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz, T _C = 120°C)	Per device Per diode	I _{FRM}	60 30	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I _{FSM}	160	А
Operating Junction Temperature		TJ	-40 to +150	°C
Storage Temperature		T _{stg}	-40 to +150	°C
Voltage Rate of Change (Rated V _R)		dv/dt	10,000	V/µs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating	Symbol	NTST30U100CTG, NTSB30U100CT-1G	NTSB30U100CTG	NTSJ30U100CTG	Unit
Maximum Thermal Resistance per Diode Junction-to-Case Junction-to-Ambient	$egin{array}{c} R_{ hetaJC} \ R_{ hetaJA} \end{array}$	2.5 70	0.93 46.5	3.81 105	°C/W

ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

Rating	Symbol	Тур	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1)	V _F	0.47 0.52 0.66	- - 0.80	V
$(I_F = 5 \text{ A}, T_J = 125^{\circ}\text{C})$ $(I_F = 7.5 \text{ A}, T_J = 125^{\circ}\text{C})$ $(I_F = 15 \text{ A}, T_J = 125^{\circ}\text{C})$		0.42 0.48 0.60	- - 0.65	
Maximum Instantaneous Reverse Current (Note 1) $ (V_R = 70 \text{ V}, T_J = 25^{\circ}\text{C}) $ $ (V_R = 70 \text{ V}, T_J = 125^{\circ}\text{C}) $	I _R	15 12		μA mA
(Rated dc Voltage, $T_J = 25^{\circ}C$) (Rated dc Voltage, $T_J = 125^{\circ}C$)		65 32	675 60	μA mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Pulse Test: Pulse Width = $300 \,\mu s$, Duty Cycle $\leq 2.0\%$

TYPICAL CHARACTERISITICS

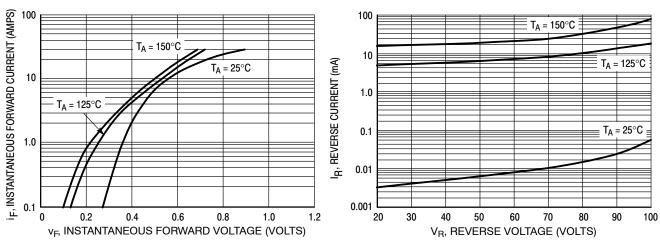


Figure 1. Typical Forward Voltage

Figure 2. Typical Reverse Current

140

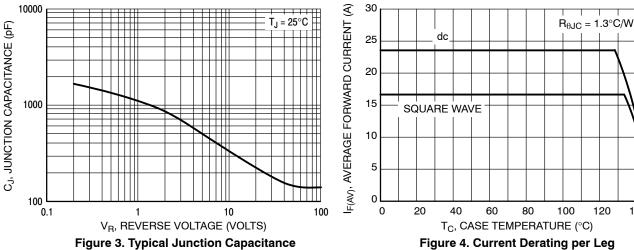


Figure 3. Typical Junction Capacitance

60

55

50

45

40

35 30

25

20

15

10 5

0

dc

SQUARE WAVE

I_{F(AV)}, AVERAGE FORWARD CURRENT (A)

30 P_{F(AV)}, AVERAGE FORWARD POW-ER DISSIPATION (W) $I_{PK}/I_{AV} = 10$ $I_{PK}/I_{AV} = 5$ $I_{PK}/I_{AV} = 20$ 20 QUARE **WAVE** 10 dc T_A = 150°C 0 10 12 16 $I_{F(AV)}$, AVERAGE FORWARD CURRENT (A)

 $R_{\theta JC} = 1.3^{\circ}C/W$

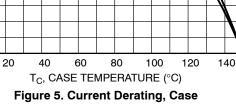


Figure 6. Forward Power Dissipation

TYPICAL CHARACTERISITICS

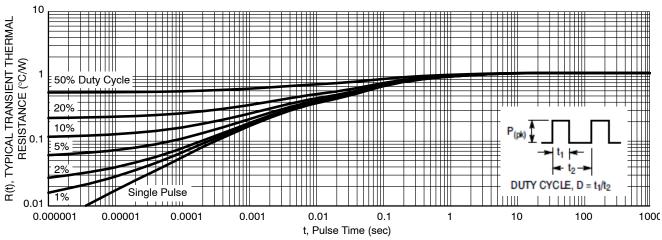


Figure 7. Typical Transient Thermal Response, Junction-to-Case for NTST30U100CT and NTSB30U100CT-1G

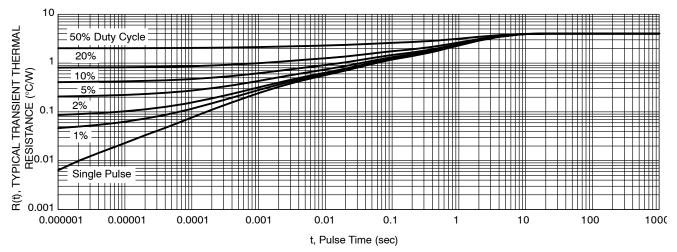


Figure 8. Typical Transient Thermal Response, Junction-to-Case for NTSJ30U100CTG

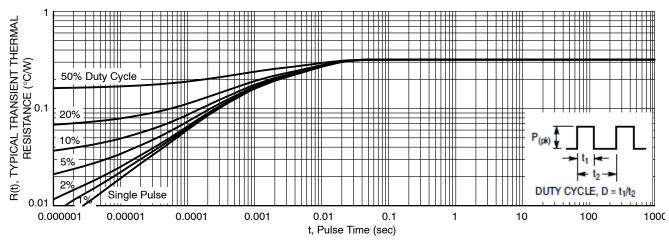


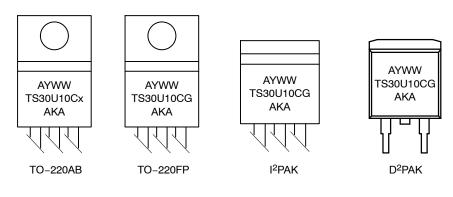
Figure 9. Typical Transient Thermal Response, Junction-to-Case for NTSB30U100CTG

ORDERING INFORMATION

Device	Package	Shipping [†]
NTST30U100CTG	TO-220AB (Pb-Free)	50 Units / Rail
NTST30U100CTH	TO-220AB (Halide-Free)	50 Units / Rail
NTSB30U100CT-1G	I ² PAK (Pb-Free)	50 Units / Rail
NTSJ30U100CTG	TO-220FP (Halide-Free)	50 Units / Rail
NTSB30U100CTG	D ² PAK (Pb-Free)	50 Units / Rail
NTSB30U100CTT4G	D ² PAK (Pb-Free)	800 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MARKING DIAGRAMS



A = Assembly Location

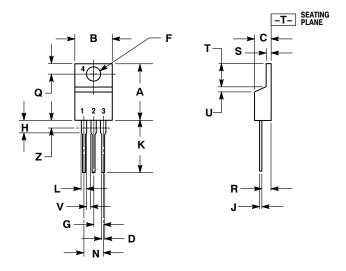
Y = Year WW = Work Week AKA = Polarity Designator

x = G or H

G = Pb-Free Package H = Halide-Free Package

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AH**



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

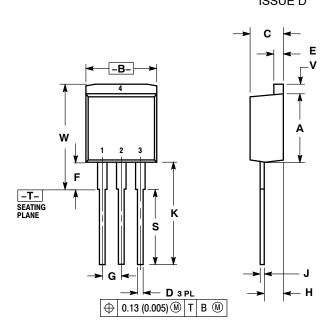
 2. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 6: PIN 1. ANODE

- 2. CATHODE 3. ANODE 4. CATHODE

I²PAK (TO-262) CASE 418D ISSUE D



- OTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

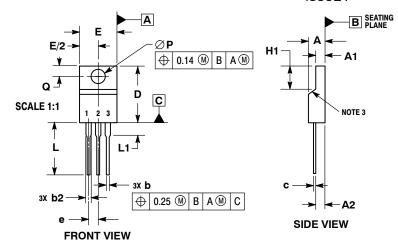
	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.335	0.380	8.51	9.65
В	0.380	0.406	9.65	10.31
С	0.160	0.185	4.06	4.70
D	0.026	0.035	0.66	0.89
Е	0.045	0.055	1.14	1.40
F	0.122 REF		3.10 REF	
G	0.100 BSC		2.54 BSC	
Н	0.094	0.110	2.39	2.79
J	0.013	0.025	0.33	0.64
K	0.500	0.562	12.70	14.27
S	0.390 REF		9.90	REF
٧	0.045	0.070	1.14	1.78
W	0.522	0.551	13.25	14.00

- STYLE 3:
 PIN 1. ANODE
 2. CATHODE
 3. ANODE
 4. CATHODE

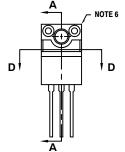
PACKAGE DIMENSIONS

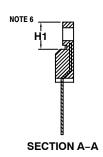
TO-220 FULLPACK, 3-LEAD

CASE 221AH **ISSUE F**









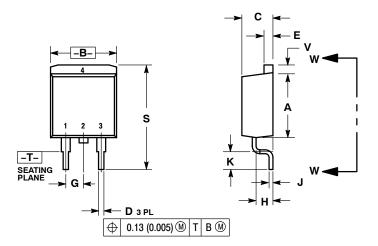
ALTERNATE CONSTRUCTION

- DIMENSIONING AND TOLERANCING PER ASME
- Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
- 2. CONTHOLLING DIMENSION: MILLIMETERS.
 3. CONTOUR UNCONTROLLED IN THIS AREA.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
 5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION.
- DIMENSION 02 DUES NOT INCLUDE DAMBAR PROTHOSION.
 LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
 CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY MAY VARY WITHIN THE ENVELOP DEFINED BY DIMENSIONS AT AND H1 FOR MANUFACTURING PURPOSES.

	MILLIMETERS			
DIM	MIN	MAX		
Α	4.30	4.70		
A1	2.50	2.90		
A2	2.50	2.90		
b	0.54	0.84		
b2	1.10	1.40		
С	0.49	0.79		
D	14.70	15.30		
Е	9.70	10.30		
е	2.54	BSC		
H1	6.60	7.10		
L	12.50	14.73		
L1		2.80		
P	3.00	3.40		
Q	2.80	3.20		

PACKAGE DIMENSIONS

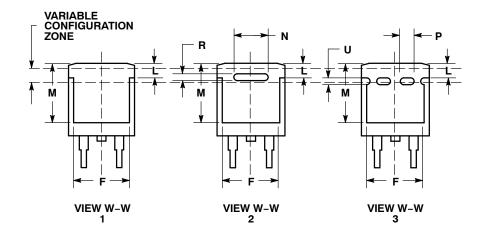
D²PAK 3 CASE 418B-04 ISSUE K



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14 5M 1982
- 2. CONTROLLING DIMENSION: INCH.
- 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.340	0.380	8.64	9.65
В	0.380	0.405	9.65	10.29
С	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
Н	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
Р	0.079 REF		2.00 REF	
R	0.039	REF	0.99	REF
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40



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